

Amendments to the Claims

This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

Claim 1 (Currently Amended): A method of manufacturing a semiconductor device, comprising:

forming a gate insulating film on a first conductivity type layer of a semiconductor substrate;

forming on the gate insulating film, a gate electrode having slits at, at least, one ~~end thereof on the drain electrode-forming predeterminate side;~~

selectively implanting a second conductivity type impurity in the first conductivity type layer with the gate electrode as a mask; and

effecting heat treatment to activate the impurity and integrating impurity regions in which the impurity is implanted in the slits, and impurity regions in the neighborhood of the slits~~[[,]] in which the impurity is implanted in portions outside the gate electrode,~~ thereby forming a pair of second conductivity type layers which overlap with the gate electrode ~~[[on]], at the [[least]] one end thereof sides on the drain electrode-forming predeterminate side, of the gate electrode;~~ and

forming within the pair of second conductivity type layers, a pair of second conductivity type high-density layers which are spaced away from the gate electrode

~~and adapted to contact source and drain electrodes respectively.~~

Claim 2 (Currently Amended): The method according to claim 1, wherein ~~[[the]]~~ length from an end of each of the slits to an end of the gate electrode in the vicinity of the slits ~~[[slit]]~~ is formed to a length in which the impurity regions ~~region~~ in which the impurity is implanted in the slits ~~[[slit]]~~ and the impurity regions ~~region~~ in the neighborhood of the ~~[[slit,]]~~ slits in which the impurity is implanted in the ~~corresponding portion~~ portions outside the gate electrode, are integrated by transverse diffusion based on heat treatment.

Claim 3 (Currently Amended): A semiconductor device comprising:

a pair of second conductivity type layers formed away from each other within a first conductivity type layer of a semiconductor substrate;

a gate insulating film formed over the first conductivity type layer and the pair of second conductivity type layers;

a gate electrode formed on the gate insulating film so as to connect the pair of second conductivity type layers and overlap with the second conductivity layers on, at least, one side of the gate electrode ~~sides on the drain electrode forming predeterminate side~~, said gate electrode having slits at portions above ends of the overlapped second conductivity type layers; and

a pair of second conductivity type high-density layers respectively formed within

the pair of second conductivity type layers so as to be spaced away from the gate electrode ~~and to contact a source electrode and a drain electrode respectively.~~

Claim 4 (Currently Amended): A semiconductor device according to claim 3, wherein the second conductivity type layers are lower in density ~~than other portions~~ at portions below ends of the gate electrode[[,]] which are located outside the slits than at other portions of the second conductivity type layers.

Claim 5 (Currently Amended): A semiconductor device according to claim 3, wherein a length in which ~~said each~~ the second conductivity type ~~[[layer]]~~ layers and the gate electrode overlap, is determined according to a device high breakdown voltage.